

2812

00862.022541.

PATENT APPLICATION



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
MASATAKA ITO)
Application No.: 10/091,461)
Filed: March 7, 2002)
For: SOI SUBSTRATE, ANNEALING)
METHOD THEREFOR,)
SEMICONDUCTOR DEVICE)
HAVING THE SOI SUBSTRATE,)
AND METHOD OF)
MANUFACTURING THE SAME : Date: June 21, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449. Copies of the listed documents are also enclosed.

The listed documents were cited in a Search Report which issued in an European patent application corresponding to the subject application. A copy of the European Search Report, which is dated May 24, 2005, is enclosed.

The Sasaki article includes an English-language abstract.

STATEMENT UNDER 37 C.F.R. § 1.97(e)

Each item of information in this Information Disclosure Statement was first cited in any communication from a foreign Patent Office in a counterpart foreign application not more than three months prior to the filing date of this Statement.

FORMAL MATTERS

No fee is believed due; however, any fee required in connection with this paper should be charged to Deposit Account No. 06-1205.

CONCLUSION

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicant's undersigned attorney may be reached in our Costa Mesa, California office by telephone at (714) 540-8700. All correspondence should continue to be directed to our address given below.

Respectfully submitted,

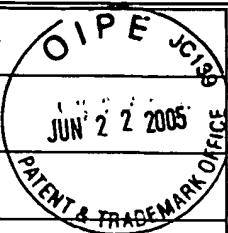


Damond E. Vadnais
Attorney for Applicant
Registration No.: 52,310

FITZPATRICK, CELLA, HARPER & SCINTO
30 Rockefeller Plaza
New York, New York 10112-3800
Facsimile: (212) 218-2200

ATTY DOCKET NO.
00862.022541.APPLICATION NO.
10/091,461APPLICANT
MASATAKA ITOFILING DATE
March 7, 2002GROUP
2812

JUN 22 2005



U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
		0 926 707	06/30/1999	EP			
		0 926 718	06/30/1999	EP			
		0 817 248	01/07/1998	EP			

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

		H. Aga, et al., "Study of HF Defects in Thin, Bonded Silicon-on-Insulator Dependent on Original Wafers", Jpn. J. Appl. Phys., Vol. 38, May 1999, pp. 2694-2698.
		G. Sasaki, et al., "Microstructure Around Indentation of Chemical Vapor Deposition (CVD)-SiC Observed by Transmission Electron Microscopy", Yogyo-Kyokai-Shi Japan, Vol. 94, No. 8, 1986, pp. 779-783.

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 1 of 1